# **74AUP1G97**

# **Low-power configurable multiple function gate**Rev. 8 — 15 August 2012 P

**Product data sheet** 

#### **General description** 1.

The 74AUP1G97 provides configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions MUX, AND, OR, NAND, NOR, inverter and buffer. All inputs can be connected to V<sub>CC</sub> or GND.

This device ensures a very low static and dynamic power consumption across the entire V<sub>CC</sub> range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I<sub>OFF</sub>.

The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74AUP1G97 has Schmitt trigger inputs making it capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage  $V_{T+}$  and the negative voltage  $V_{T-}$  is defined as the input hysteresis voltage V<sub>H</sub>.

#### **Features and benefits** 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
  - ◆ HBM JESD22-A114F exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



## Low-power configurable multiple function gate

# 3. Ordering information

Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74AUP1G97GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363				
74AUP1G97GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886				
74AUP1G97GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891				
74AUP1G97GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115				
74AUP1G97GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 $\times$ 1.0 $\times$ 0.35 mm	SOT1202				

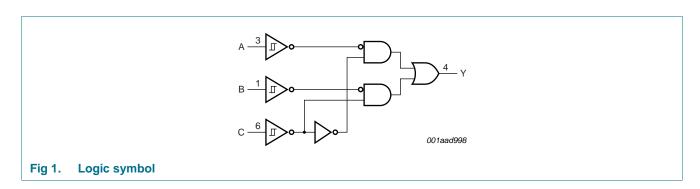
## 4. Marking

#### Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP1G97GW	aV
74AUP1G97GM	aV
74AUP1G97GF	aV
74AUP1G97GN	aV
74AUP1G97GS	aV

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

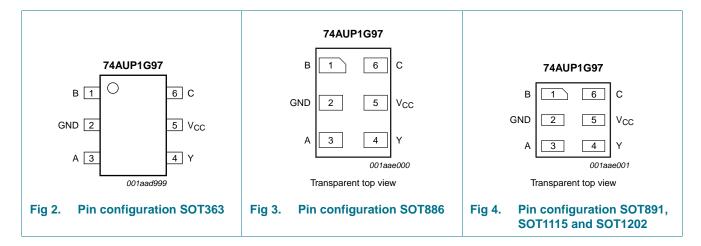
## 5. Functional diagram



Low-power configurable multiple function gate

# 6. Pinning information

#### 6.1 Pinning



#### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
В	1	data input
GND	2	ground (0 V)
А	3	data input
Υ	4	data output
V <sub>CC</sub>	5	supply voltage
С	6	data input

## 7. Functional description

Table 4. Function table[1]

Input			Output
С	В	Α	Υ
L	L	L	L
L	L	Н	L
L	Н	L	Н
L	Н	Н	Н
Н	L	L	L
Н	L	Н	Н
Н	Н	L	L
Н	Н	Н	Н

<sup>[1]</sup> H = HIGH voltage level;

L = LOW voltage level.

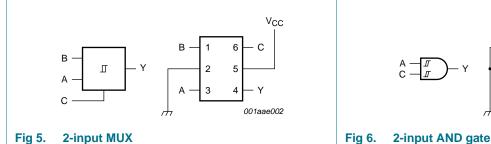
74AUP1G97

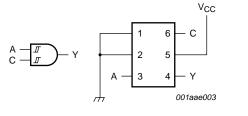
## Low-power configurable multiple function gate

## 7.1 Logic configurations

Table 5. Function selection table

Logic function	Figure
2-input MUX	see Figure 5
2-input AND	see Figure 6
2-input OR with one input inverted	see Figure 7
2-input NAND with one input inverted	see Figure 7
2-input AND with one input inverted	see Figure 8
2-input NOR with one input inverted	see Figure 8
2-input OR	see Figure 9
Inverter	see Figure 10
Buffer	see Figure 11





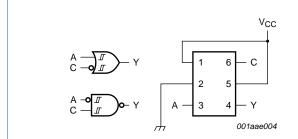


Fig 7. 2-input NAND gate with input A inverted or 2-input OR gate with input C inverted

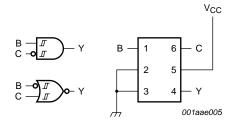


Fig 8. 2-input NOR gate with input B inverted or 2-input AND gate with input C inverted

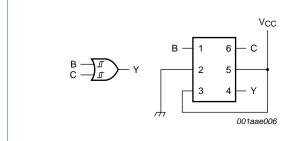


Fig 9. 2-input OR gate

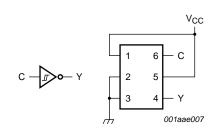
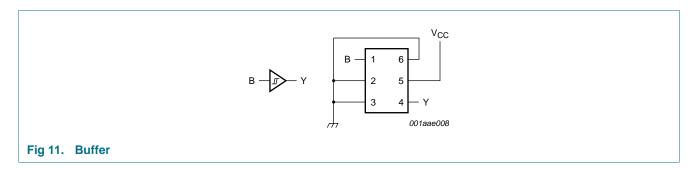


Fig 10. Inverter

#### Low-power configurable multiple function gate



## 8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	<b>–50</b>	-	mA
$V_{I}$	input voltage		<u>[1]</u> –0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	<b>–50</b>	-	mA
V <sub>O</sub>	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	50	mA
$I_{GND}$	ground current		<b>–50</b>	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2] -	250	mW

<sup>[1]</sup> The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

## 9. Recommended operating conditions

Table 7. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0 \text{ V}$	0	3.6	V
$T_{amb}$	ambient temperature		-40	+125	°C

<sup>[2]</sup> For SC-88 packages: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## Low-power configurable multiple function gate

## 10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O} = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.75V <sub>CC</sub>	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = 20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3V <sub>CC</sub>	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l <sub>l</sub>	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ
l <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I <sub>CC</sub>	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
Δl <sub>CC</sub>	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	40	μА
C <sub>I</sub>	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$	-	1.1	-	pF
Co	output capacitance	$V_O = GND$ ; $V_{CC} = 0 V$	-	1.7	-	pF
	40 °C to +85 °C					
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O} = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V <sub>CC</sub> - 0.1	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.7V <sub>CC</sub>	-	-	V
		$I_O = -1.7 \text{ mA}$ ; $V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{\rm O} = -1.9$ mA; $V_{\rm CC} = 1.65$ V	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA; } V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{\rm O} = -2.7$ mA; $V_{\rm CC} = 3.0$ V	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
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## Low-power configurable multiple function gate

**Table 8. Static characteristics** ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{OL}$	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = 20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3V <sub>CC</sub>	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I <sub>I</sub>	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μА
I <sub>CC</sub>	supply current	$V_I$ = GND or $V_{CC}$ ; $I_O$ = 0 A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.9	μА
Δl <sub>CC</sub>	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	50	μА
T <sub>amb</sub> = -	40 °C to +125 °C					
V <sub>OH</sub> I	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V <sub>CC</sub> - 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.6V <sub>CC</sub>	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = 20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.33V <sub>CC</sub>	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l <sub>l</sub>	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ

## Low-power configurable multiple function gate

 Table 8.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I <sub>CC</sub>	supply current	$V_I$ = GND or $V_{CC}$ ; $I_O$ = 0 A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	1.4	μΑ
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	75	μΑ

<sup>[1]</sup> One input at  $V_{CC}$  – 0.6 V, other input at  $V_{CC}$  or GND.

## 11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

Parameter	Conditions		25 °C			-40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
Ė		'					'	1	
propagation delay	A, B, C to Y; see Figure 12	[2]							
	$V_{CC} = 0.8 \text{ V}$		-	23.0	-	-	-	-	ns
	$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.8	6.6	12.6	2.5	13.0	13.2	ns
	$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.3	4.7	7.6	2.5	8.2	8.6	ns
	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.2	3.9	6.2	2.0	6.8	7.2	ns
	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	3.2	4.5	1.7	5.1	5.3	ns
	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.9	2.9	3.9	1.5	4.1	4.3	ns
o <b>F</b>									
propagation delay	A, B, C to Y; see Figure 12	[2]							
	$V_{CC} = 0.8 \text{ V}$		-	26.6	-	-	-	-	ns
	$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.2	7.4	14.3	2.9	14.9	15.2	ns
	$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.6	5.3	8.7	2.8	9.4	9.8	ns
	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.5	4.5	7.0	2.3	7.8	8.2	ns
	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.4	3.7	5.2	2.1	5.9	6.1	ns
	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.3	3.4	4.6	1.9	4.9	5.1	ns
o <b>F</b>									
propagation delay	A, B, C to Y; see Figure 12	[2]							
	$V_{CC} = 0.8 \text{ V}$		-	30.1	-	-	-	-	ns
	$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.6	8.2	16.0	3.2	16.7	17.0	ns
	$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.9	5.9	9.6	3.1	10.4	10.9	ns
	$V_{CC}$ = 1.65 V to 1.95 V		2.8	5.0	7.8	2.5	8.7	9.1	ns
	$V_{CC}$ = 2.3 V to 2.7 V		2.7	4.2	5.8	2.4	6.5	6.9	ns
	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.5	3.8	5.1	2.2	5.5	5.7	ns
	propagation delay  F  propagation delay	propagation delay A, B, C to Y; see Figure 12 $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ Propagation delay A, B, C to Y; see Figure 12 $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ Propagation delay A, B, C to Y; see Figure 12 $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.3 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.3 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	propagation delay A, B, C to Y; see Figure 12 $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ Propagation delay A, B, C to Y; see Figure 12 $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ Propagation delay A, B, C to Y; see Figure 12 $V_{CC} = 0.8 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.3 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.3 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	propagation delay	Propagation delay Propagation	Propagation delay   A, B, C to Y; see Figure 12   2    V <sub>CC</sub> = 0.8 V   - 23.0   - 23	Propagation delay Propagation	Min   Typ[1]   Max   Min   Max (85 °C)	Propagation delay   A, B, C to Y; see Figure 12   22

## Low-power configurable multiple function gate

 Table 9.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

Symbol	Parameter	Conditions		25 °C		-4	0 °C to +1	25 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 30	pF		·	'		'	1	'	1
t <sub>pd</sub>	propagation delay	A, B, C to Y; see Figure 12	[2]						
		$V_{CC} = 0.8 \text{ V}$	-	38.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	4.6	10.5	20.9	4.0	21.8	22.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	3.7	7.4	12.2	3.8	13.3	14.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	3.5	6.3	9.9	3.2	11.1	11.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	3.4	5.3	7.4	3.1	8.3	8.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	3.2	4.9	6.6	2.8	7.0	7.4	ns
C <sub>L</sub> = 5 p	oF, 10 pF, 15 pF and	30 pF							
$C_{PD}$		$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3]						
	capacitance	$V_{CC} = 0.8 \text{ V}$	-	2.6	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	2.8	-	-	-	-	рF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	2.9	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	3.1	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	3.7	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	4.3	-	-	-	-	рF

<sup>[1]</sup> All typical values are measured at nominal V<sub>CC</sub>.

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$$

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

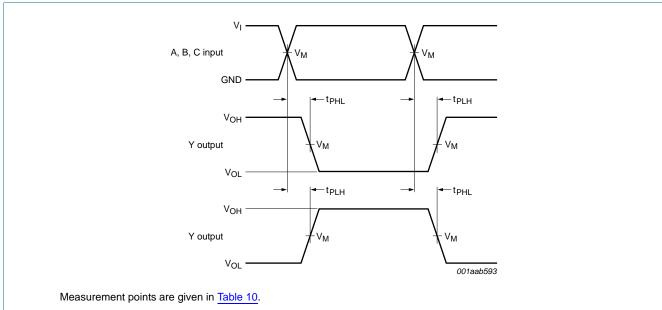
 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$  = sum of the outputs.

<sup>[2]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ 

<sup>[3]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

## Low-power configurable multiple function gate

## 12. Waveforms



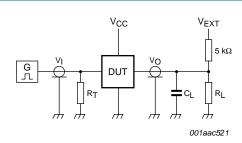
 $\ensuremath{V_{OL}}$  and  $\ensuremath{V_{OH}}$  are typical output voltage drop that occur with the output load.

Fig 12. Input A, B and C to output Y propagation delay times

Table 10. Measurement points

Supply voltage	Output	Input		
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>I</sub>	$t_r = t_f$
0.8 V to 3.6 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	V <sub>CC</sub>	≤ 3.0 ns

#### Low-power configurable multiple function gate



Test data is given in Table 11.

Definitions for test circuit:

 $R_L$  = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to the output impedance  $Z_0$  of the pulse generator.

V<sub>EXT</sub> = External voltage for measuring switching times.

Fig 13. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Load		V <sub>EXT</sub>		
V <sub>CC</sub>	C <sub>L</sub>	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	2V <sub>CC</sub>

<sup>[1]</sup> For measuring enable and disable times  $R_L$  = 5 k $\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L$  = 1 M $\Omega$ .

## 13. Transfer characteristics

Table 12. Transfer characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see <u>Figure 13</u>.

Symbol	Parameter	Conditions		25 °C		-40 °C to +125 °C			Unit
			Min	Тур	Max	Min	Max (85 °C)	Max (125 °C)	
$V_{T+}$	V <sub>T+</sub> positive-going	see Figure 14 and Figure 15							
	threshold voltage	$V_{CC} = 0.8 \text{ V}$	0.30	-	0.60	0.30	0.60	0.62	V
		V <sub>CC</sub> = 1.1 V	0.53	-	0.90	0.53	0.90	0.92	V
		V <sub>CC</sub> = 1.4 V	0.74	-	1.11	0.74	1.11	1.13	V
		V <sub>CC</sub> = 1.65 V	0.91	-	1.29	0.91	1.29	1.31	V
		V <sub>CC</sub> = 2.3 V	1.37	-	1.77	1.37	1.77	1.80	V
		V <sub>CC</sub> = 3.0 V	1.88	-	2.29	1.88	2.29	2.32	V
$V_{T-}$	negative-going	see Figure 14 and Figure 15							
	threshold voltage	V <sub>CC</sub> = 0.8 V	0.10	-	0.60	0.10	0.60	0.60	V
		V <sub>CC</sub> = 1.1 V	0.26	-	0.65	0.26	0.65	0.65	V
		V <sub>CC</sub> = 1.4 V	0.39	-	0.75	0.39	0.75	0.75	V
		V <sub>CC</sub> = 1.65 V	0.47	-	0.84	0.47	0.84	0.84	V
		V <sub>CC</sub> = 2.3 V	0.69	-	1.04	0.69	1.04	1.04	V
	V <sub>CC</sub> = 3.0 V	0.88	-	1.24	0.88	1.24	1.24	V	

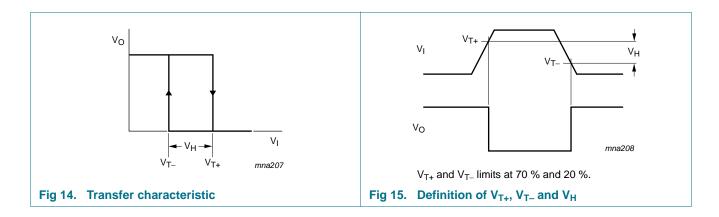
## Low-power configurable multiple function gate

 Table 12.
 Transfer characteristics ...continued

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 13.

Symbol	Parameter	Conditions		25 °C		-40 °C to +125 °C			Unit
			Min	Тур	Max	Min	Max (85 °C)	Max (125 °C)	
$V_{H}$	hysteresis voltage	(V <sub>T+</sub> – V <sub>T-</sub> ); see <u>Figure 14</u> , <u>Figure 15</u> , <u>Figure 16</u> and <u>Figure 17</u>							
	V <sub>CC</sub> = 0.8 V	0.07	-	0.50	0.07	0.50	0.50	V	
	V <sub>CC</sub> = 1.1 V	0.08	-	0.46	0.08	0.46	0.46	V	
	V <sub>CC</sub> = 1.4 V	0.18	-	0.56	0.18	0.56	0.56	V	
	V <sub>CC</sub> = 1.65 V	0.27	-	0.66	0.27	0.66	0.66	V	
	V <sub>CC</sub> = 2.3 V	0.53	-	0.92	0.53	0.92	0.92	V	
		V <sub>CC</sub> = 3.0 V	0.79	-	1.31	0.79	1.31	1.31	V

## 14. Waveforms transfer characteristics



## Low-power configurable multiple function gate

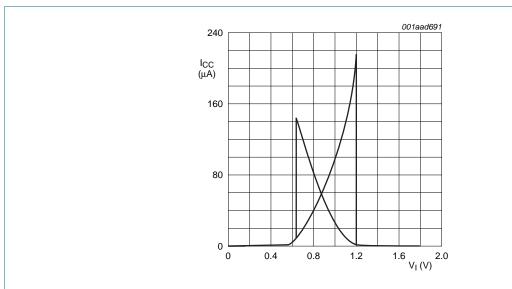


Fig 16. Typical transfer characteristics;  $V_{CC} = 1.8 \text{ V}$ 

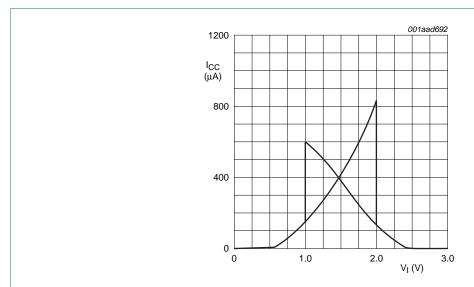


Fig 17. Typical transfer characteristics;  $V_{CC} = 3.0 \text{ V}$ 

## Low-power configurable multiple function gate

## 15. Package outline

#### Plastic surface-mounted package; 6 leads

**SOT363** 

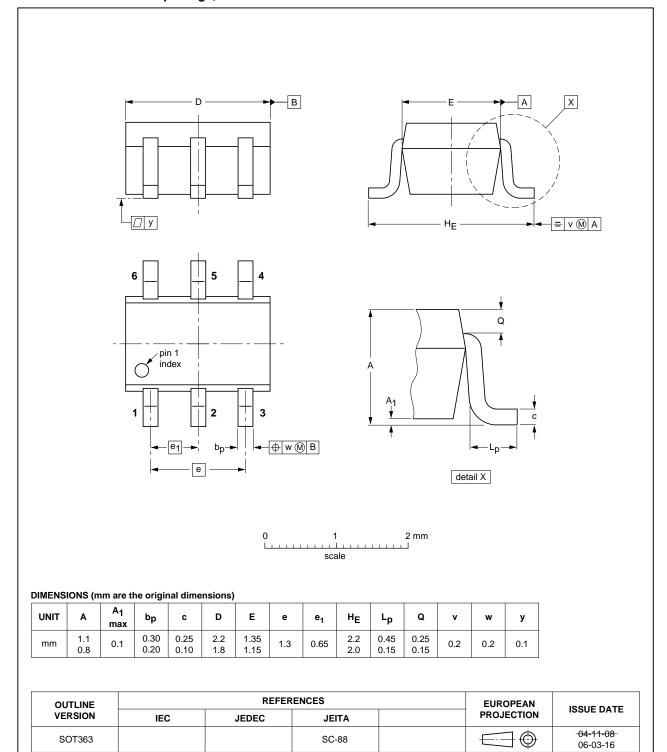


Fig 18. Package outline SOT363 (SC-88)

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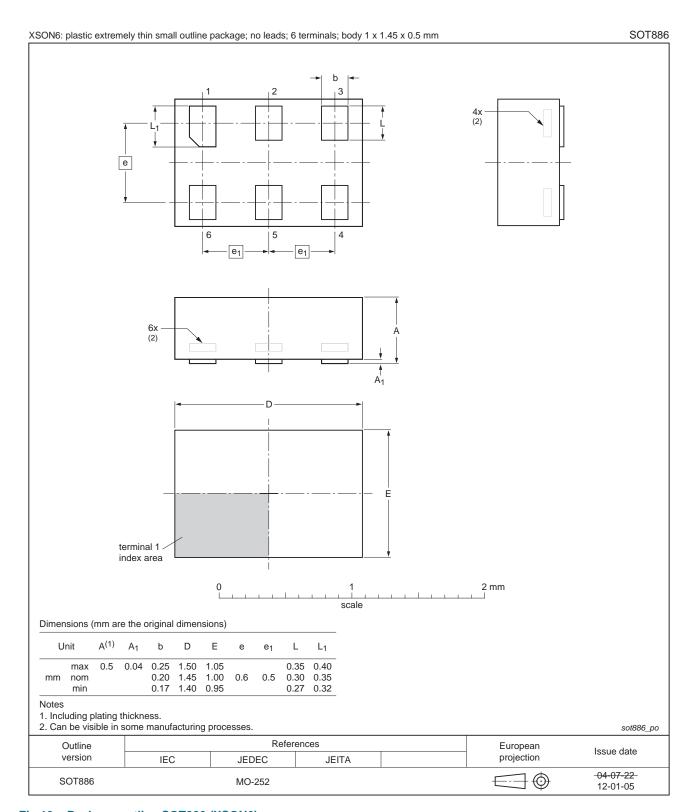


Fig 19. Package outline SOT886 (XSON6)

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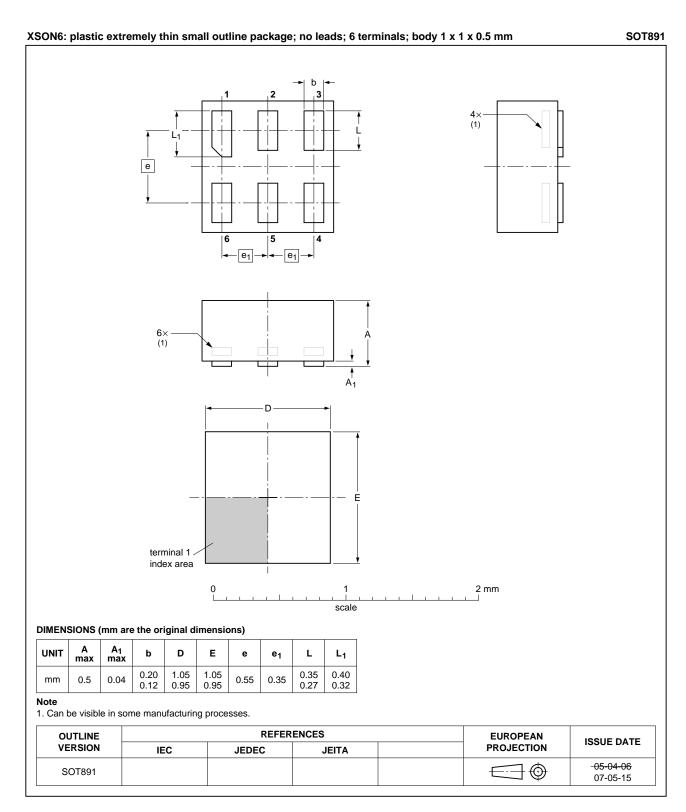


Fig 20. Package outline SOT891 (XSON6)

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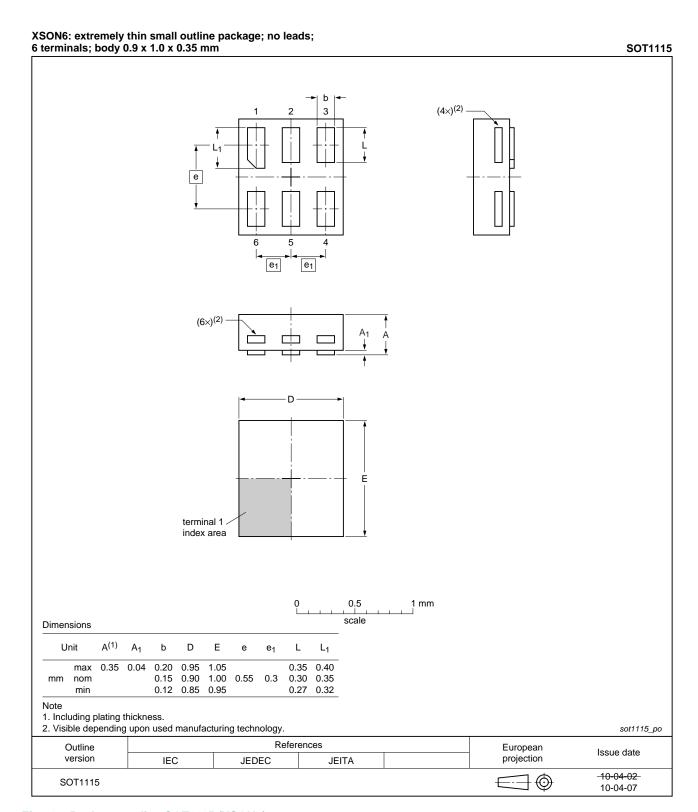


Fig 21. Package outline SOT1115 (XSON6)

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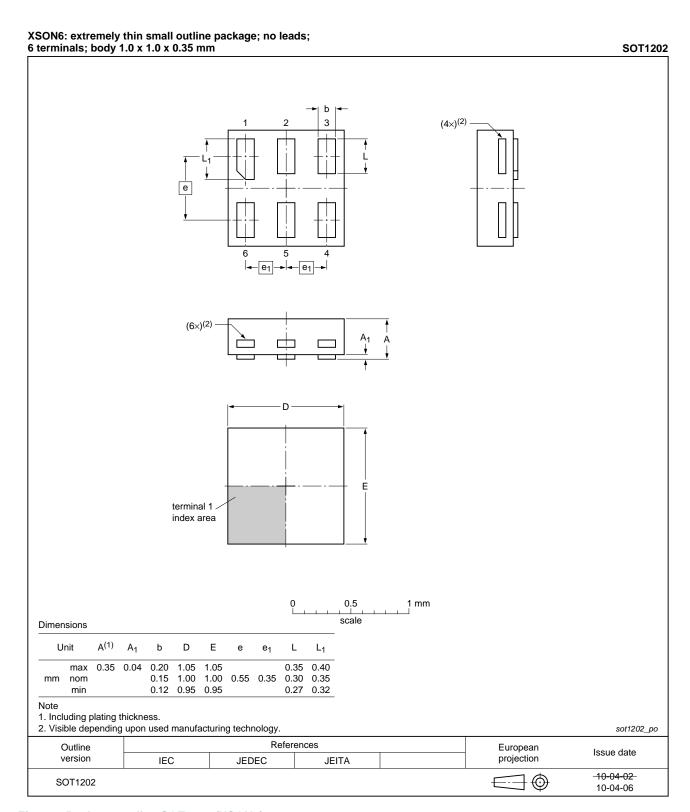


Fig 22. Package outline SOT1202 (XSON6)

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## Low-power configurable multiple function gate

## 16. Abbreviations

#### Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

# 17. Revision history

#### Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G97 v.8	20120815	Product data sheet	-	74AUP1G97 v.7
Modifications:	<ul> <li>Package outline</li> </ul>	e drawing of SOT886 (Figure 19)	modified.	
74AUP1G97 v.7	20111128	Product data sheet	-	74AUP1G97 v.6
74AUP1G97 v.6	20110110	Product data sheet	-	74AUP1G97 v.5
74AUP1G97 v.5	20101020	Product data sheet	-	74AUP1G97 v.4
74AUP1G97 v.4	20090623	Product data sheet	-	74AUP1G97 v.3
74AUP1G97 v.3	20090518	Product data sheet	-	74AUP1G97 v.2
74AUP1G97 v.2	20090327	Product data sheet	-	74AUP1G97 v.1
74AUP1G97 v.1	20061107	Product data sheet	-	-

#### Low-power configurable multiple function gate

## 18. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
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